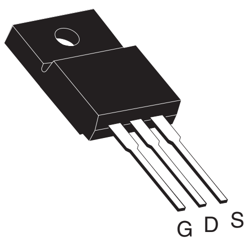
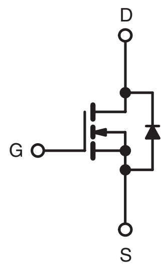
Power MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	500	
$R_{DS(on)}$ (Ω)	V_{GS} = 10 V	0.67
Q_g (Max.) (nC)	45	
Q_{gs} (nC)	13	
Q_{gd} (nC)	23	
Configuration	Single	

TO-220 FULLPAK





N-Channel MOSFET

FEATURES

- Super Fast Body Diode Eliminates the Need for External Diodes in ZVS Applications
- Lower Gate Charge Results in Simpler Drive Reqirements
- Enhanced dV/dt Capabilities Offer Improved Ruggedness
- Higher Gate Voltage Threshold Offers Improved Noise Immunity
- Lead (Pb)-free

RoHS COMPLIANT

APPLICATIONS

- Zero Voltage Switching SMPS
- Telecom and Server Power Supplies
- Uninterruptible Power Supplies
- Motor Control Applications

ORDERING INFORMATION	
Package	TO-220 FULLPAK
Lead (Pb)-free	IRFIB5N50LPbF
	SiHFIB5N50L-E3

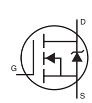
ABSOLUTE MAXIMUM RATINGS T_C = 25 °C, unless otherwise noted

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V_{DS}	500	V
Gate-Source Voltage			V_{GS}	± 30	
Continuous Drain Current	V_{GS} at 10 V	T_C = 25 °C	I_D	4.7	A
		T_C = 100 °C		3.0	
Pulsed Drain Current[a]			I_{DM}	16	
Linear Derating Factor				0.33	W/°C
Single Pulse Avalanche Energy[b]			E_{AS}	140	mJ
Avalanche Current[a]			I_{AR}	4.0	A
Repetitive Avalanche Energy[a]			E_{AR}	3.0	mJ
Maximum Power Dissipation	T_C = 25 °C		P_D	42	W
Peak Diode Recovery dV/dt[c]			dV/dt	19	V/ns
Operating Junction and Storage Temperature Range			T_J, T_{stg}	- 55 to + 150	°C
Soldering Recommendations (Peak Temperature)	for 10 s			300[d]	
Mounting Torque	6-32 or M3 screw			10	lbf · in
				1.1	N · m

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
b. Starting T_J = 25 °C, L = 18 mH, R_G = 25 Ω, I_{AS} = 4.0 A, dV/dt = 19 V/ns, (see fig. 17).
c. $I_{SD} \leq$ 4.0 A, dI/dt $\leq$ 421 A/µs, $V_{DD} \leq V_{DS}$, $T_J \leq$ 150 °C.
d. 1.6 mm from case.

THERMAL RESISTANCE RATINGS				
PARAMETER	**SYMBOL**	**TYP.**	**MAX.**	**UNIT**
Maximum Junction-to-Ambient	R_{thJA}	-	65	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	3.0	

SPECIFICATIONS T_J = 25 °C, unless otherwise noted							
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static							
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA		500	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to 25 °C, I_D = 1 mA		-	0.43	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 250 µA		3.0	-	5.0	V
Gate-Source Leakage	I_{GSS}	V_{GS} = ± 30 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 500 V, V_{GS} = 0 V		-	-	50	µA
		V_{DS} = 400 V, V_{GS} = 0 V, T_J = 125 °C		-	-	2.0	mA
Drain-Source On-State Resistance	$R_{DS(on)}$	V_{GS} = 10 V	I_D = 2.4 A[b]	-	0.67	0.80	Ω
Forward Transconductance	g_{fs}	V_{DS} = 50 V, I_D = 2.4 A		2.8	-	-	S
Dynamic							
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1.0 MHz, see fig. 5		-	1000	-	pF
Output Capacitance	C_{oss}			-	110	-	
Reverse Transfer Capacitance	C_{rss}			-	12	-	
Output Capacitance	C_{oss}	V_{GS} = 0 V	V_{DS} = 1.0 V, f = 1.0 MHz	-	1360	-	
			V_{DS} = 400 V, f = 1.0 MHz	-	31	-	
Effective Output Capacitance	C_{oss} eff.		V_{DS} = 0 V to 400 V[c]	-	75	-	
Effective Output Capacitance (Energy Related)	C_{oss} eff. (ER)			-	55	-	
Total Gate Charge	Q_g	V_{GS} = 10 V	I_D = 4.0 A, V_{DS} = 400 V, see fig. 7 and 16[b]	-	-	45	nC
Gate-Source Charge	Q_{gs}			-	-	13	
Gate-Drain Charge	Q_{gd}			-	-	23	
Internal Gate Resistance	R_G	f = 1 MHz, open drain		-	2.0	-	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 250 V, I_D = 4.0 A, R_G = 9.0 Ω, V_{GS} = 10 V, see fig. 11a and 11b[b]		-	13	-	ns
Rise Time	t_r			-	17	-	
Turn-Off Delay Time	$t_{d(off)}$			-	26	-	
Fall Time	t_f			-	10	-	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	4.7	A
Pulsed Diode Forward Current[a]	I_{SM}			-	-	16	
Body Diode Voltage	V_{SD}	T_J = 25 °C, I_S = 4.0 A, V_{GS} = 0 V[b]		-	-	1.5	V
Body Diode Reverse Recovery Time	t_{rr}	T_J = 25 °C, I_F = 4.0 A, T_J = 125 °C, dI/dt = 100 A/µs[b]		-	73	110	ns
				-	99	150	
Body Diode Reverse Recovery Charge	Q_{rr}	T_J = 25 °C, I_S = 4.0 A, T_J = 125 °C, dI/dt = 100 A/µs[b]		-	200	310	nC
				-	360	540	
Drain-Source Body Diode Characteristics							
Body Diode Reverse Recovery Current	I_{RRM}	T_J = 25 °C		-	6.7	10	A
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)					

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
b. Pulse width ≤ 300 µs; duty cycle ≤ 2 %.
c. C_{oss} eff. is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80 % V_{DS}.
C_{oss} eff. (ER) is a fixed capacitance that stores the same energy as C_{oss} while V_{DS} is rising from 0 to 80 % V_{DS}.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

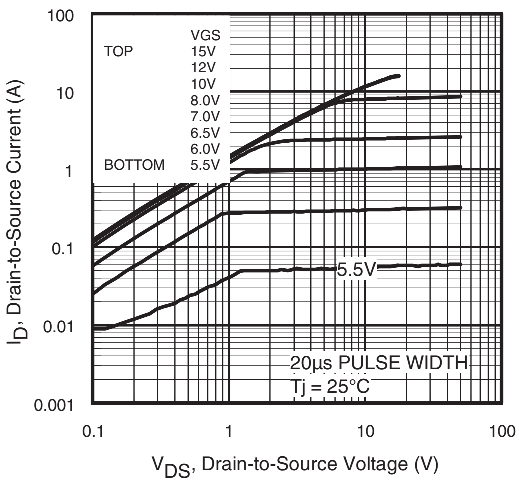


Fig. 1 - Typical Output Characteristics

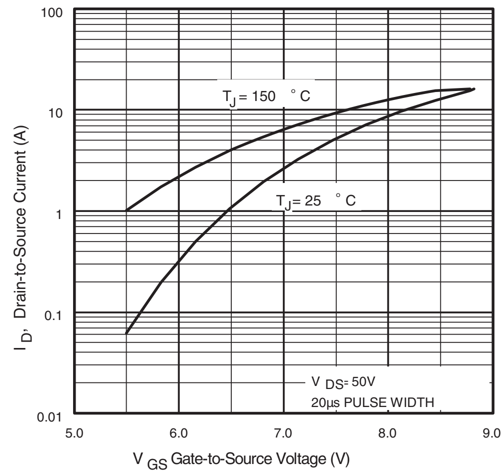


Fig. 3 - Typical Transfer Characteristics

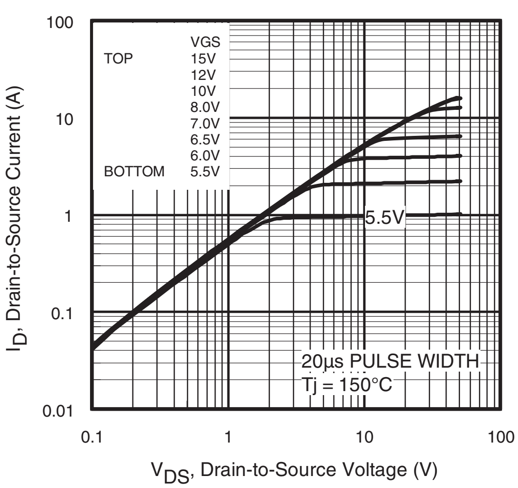


Fig. 2 - Typical Output Characteristics

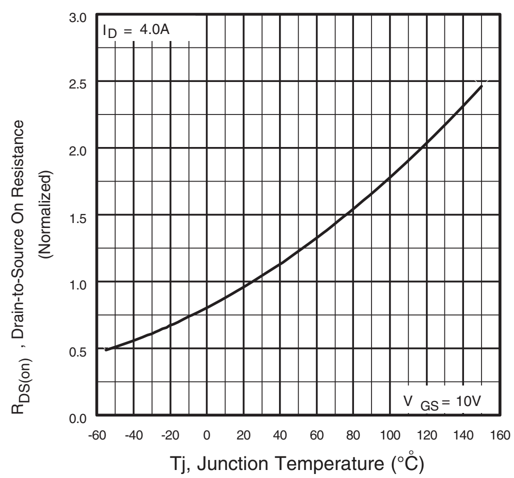


Fig. 4 - Normalized On-Resistance vs. Temperature

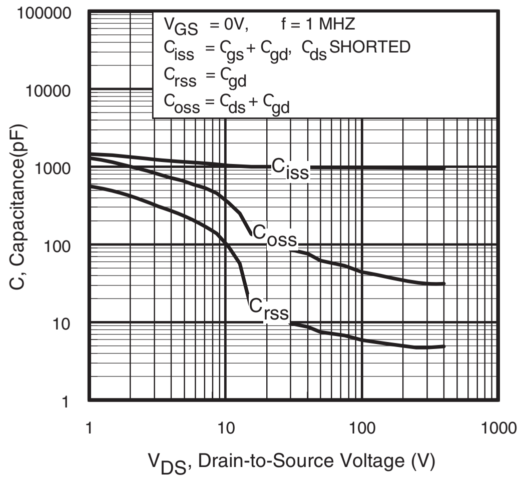


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

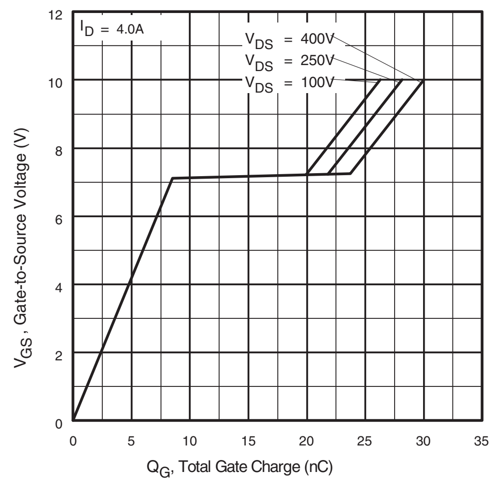


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

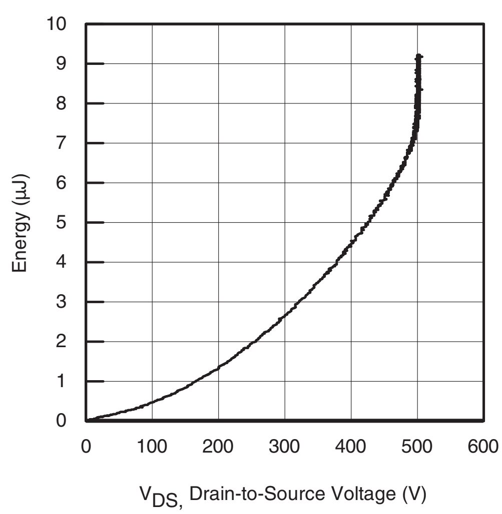


Fig. 6 - Typical Output Capacitance Stored Energy vs. V_{DS}

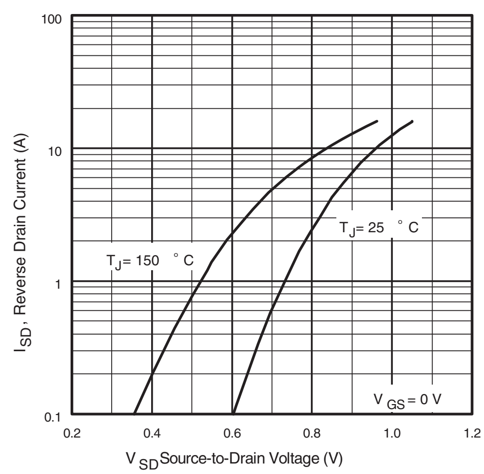


Fig. 8 - Typical Source-Drain Diode Forward Voltage

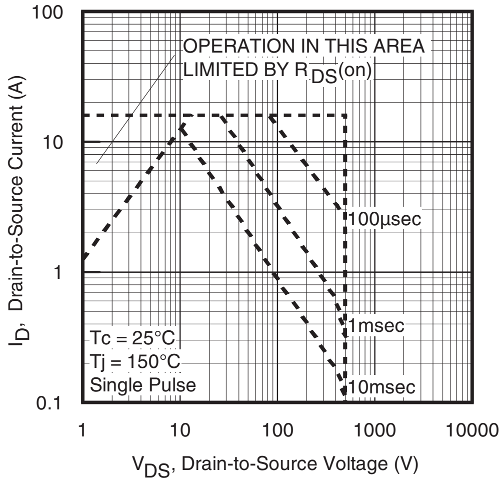


Fig. 9 - Maximum Safe Operating Area

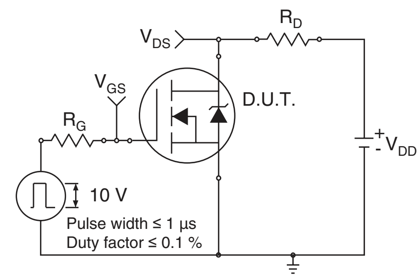


Fig. 11a - Switching Time Test Circuit

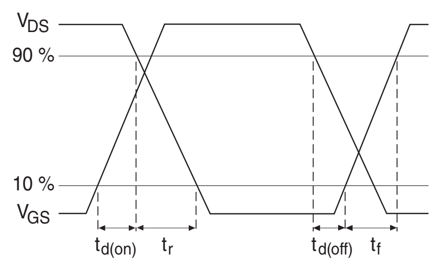


Fig. 11b - Switching Time Waveforms

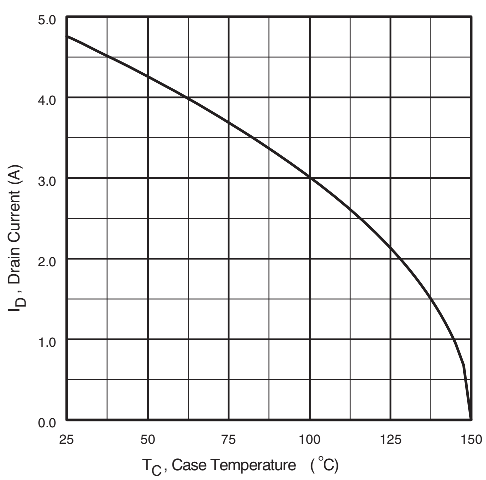


Fig. 10 - Maximum Drain Current vs. Case Temperature

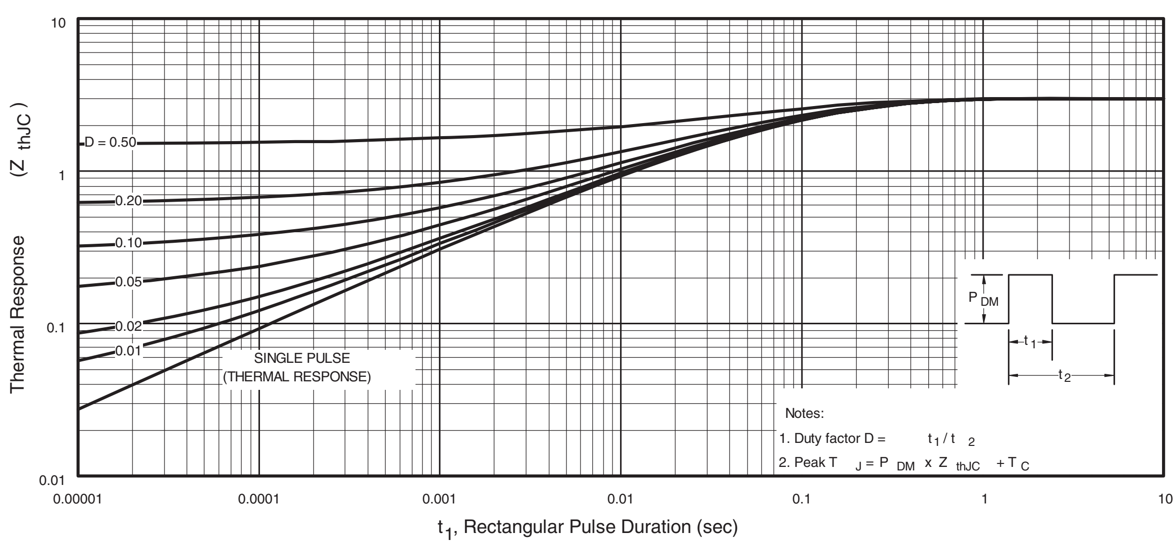


Fig. 12 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

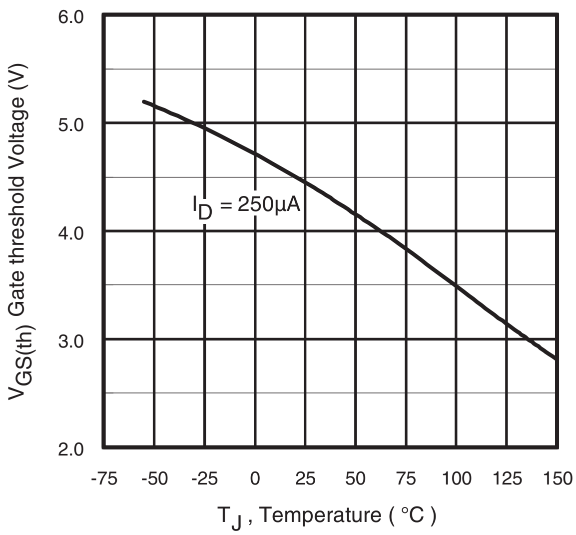


Fig. 13 - Threshold Voltage vs. Temperature

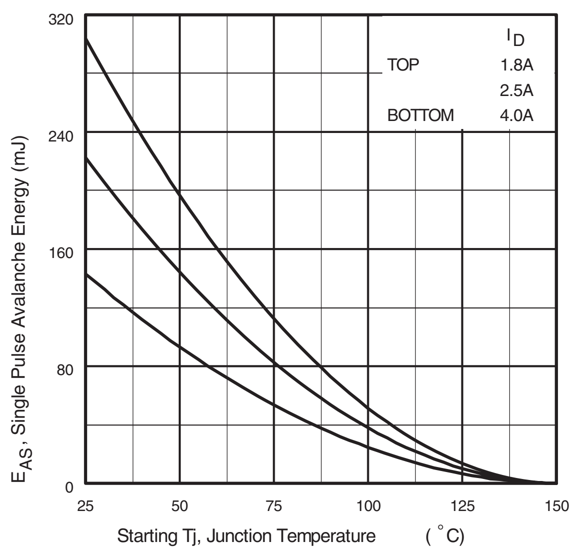


Fig. 14 - Maximum Avalanche Energy vs. Drain Current

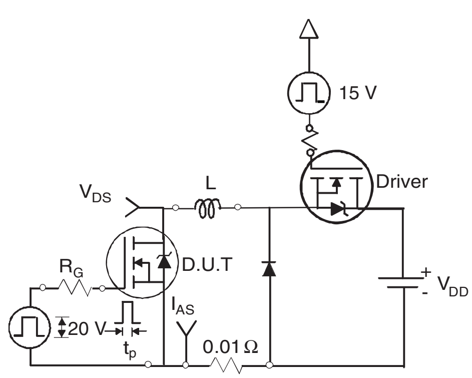


Fig. 15a - Unclamped Inductive Test Circuit

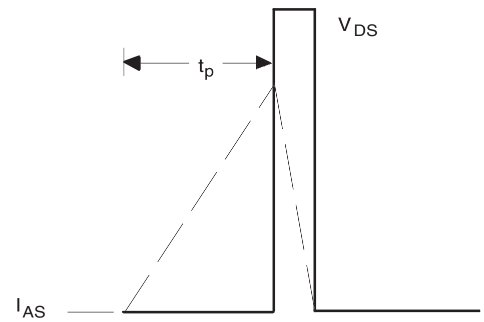


Fig. 15b - Unclamped Inductive Waveforms

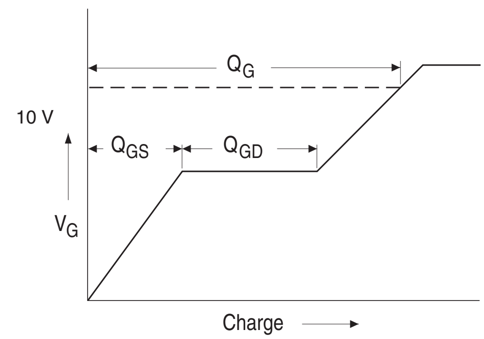


Fig. 16a - Basic Gate Charge Waveform

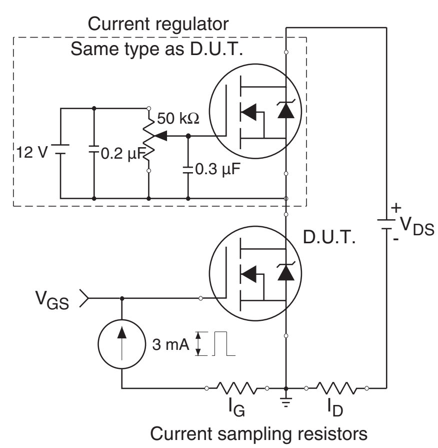
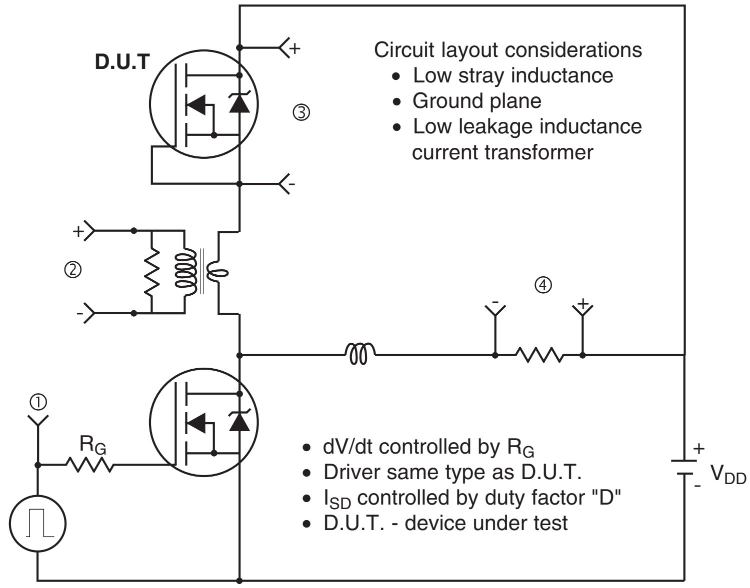
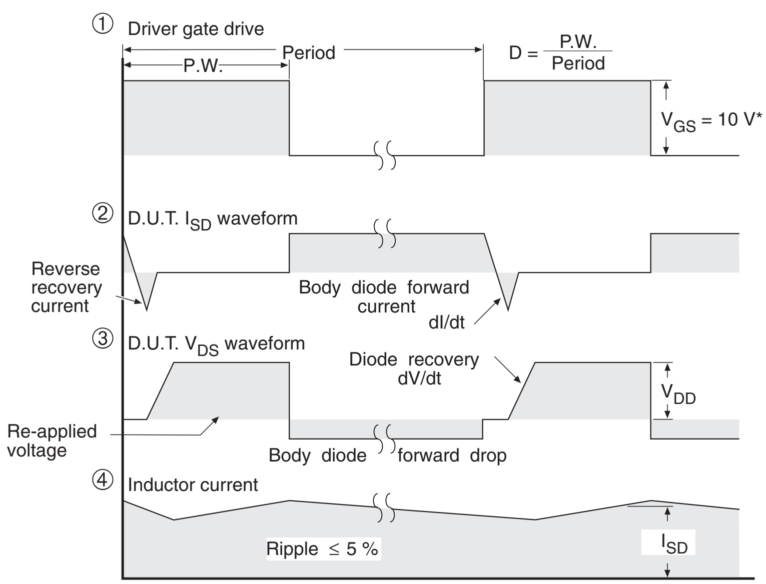


Fig. 16b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit





* V_{GS} = 5 V for logic level devices

Fig. 17 - For N-Channel

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